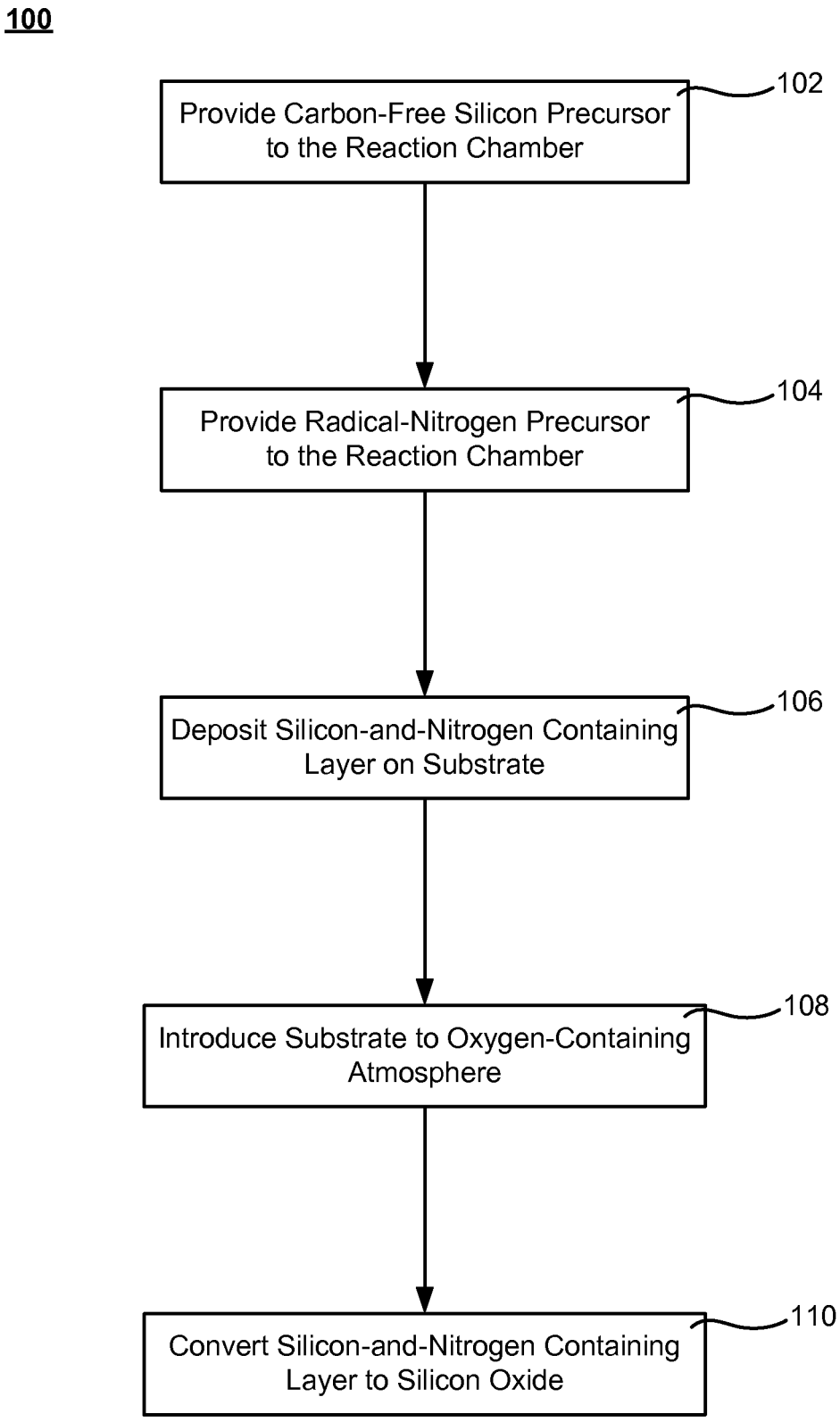

100
Provide Carbon-Free Silicon Precursor to the Reaction Chamber
102
Provide Radical-Nitrogen Precursor to the Reaction Chamber
104
Deposit Silicon-and-Nitrogen Containing Layer on Substrate
106
Introduce Substrate to Oxygen-Containing Atmosphere
108
Convert Silicon-and-Nitrogen Containing Layer to Silicon Oxide
110

FIG. 1

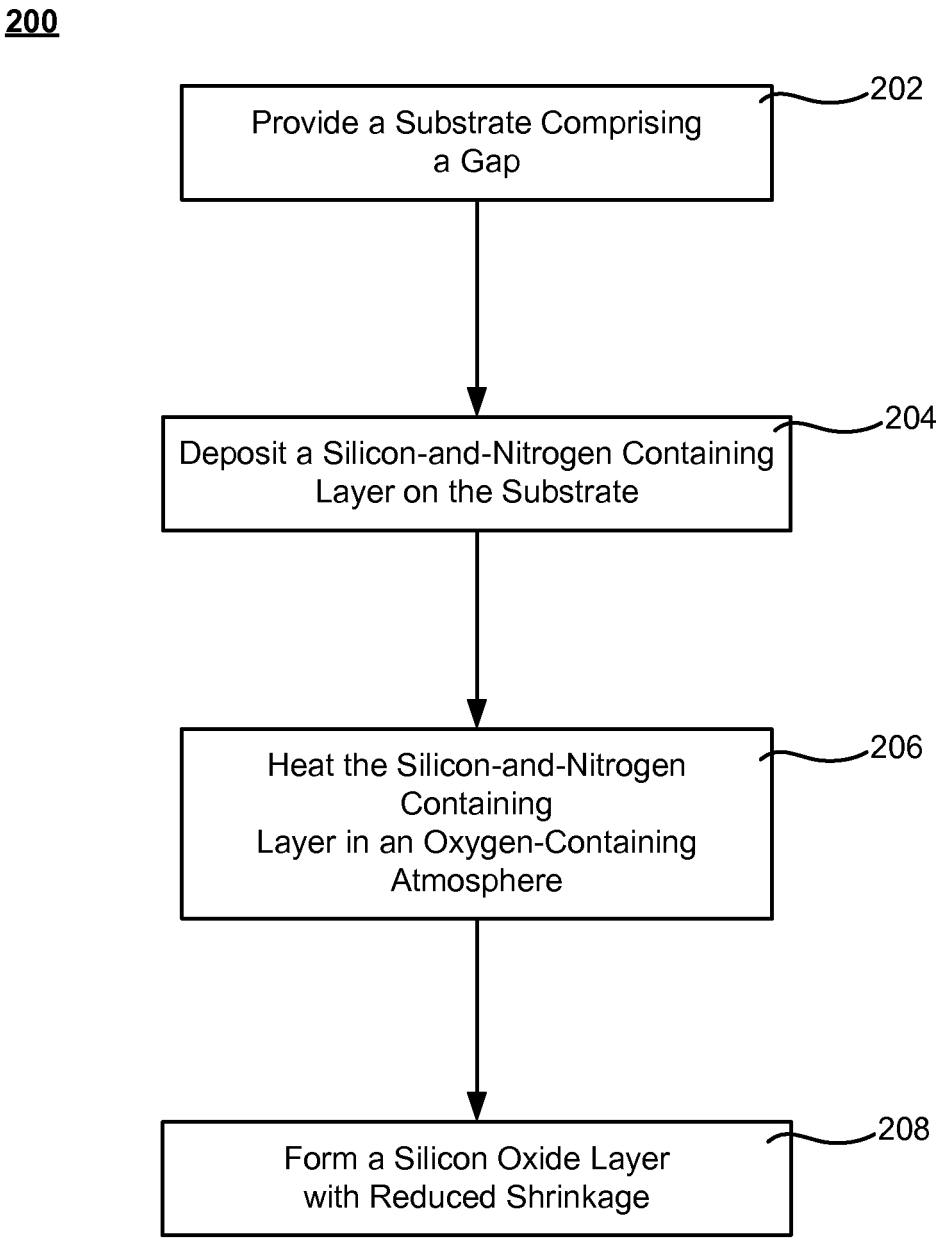

200
Provide a Substrate Comprising a Gap
202
Deposit a Silicon-and-Nitrogen Containing Layer on the Substrate
204
Heat the Silicon-and-Nitrogen Containing Layer in an Oxygen-Containing Atmosphere
206
Form a Silicon Oxide Layer with Reduced Shrinkage
208

FIG. 2

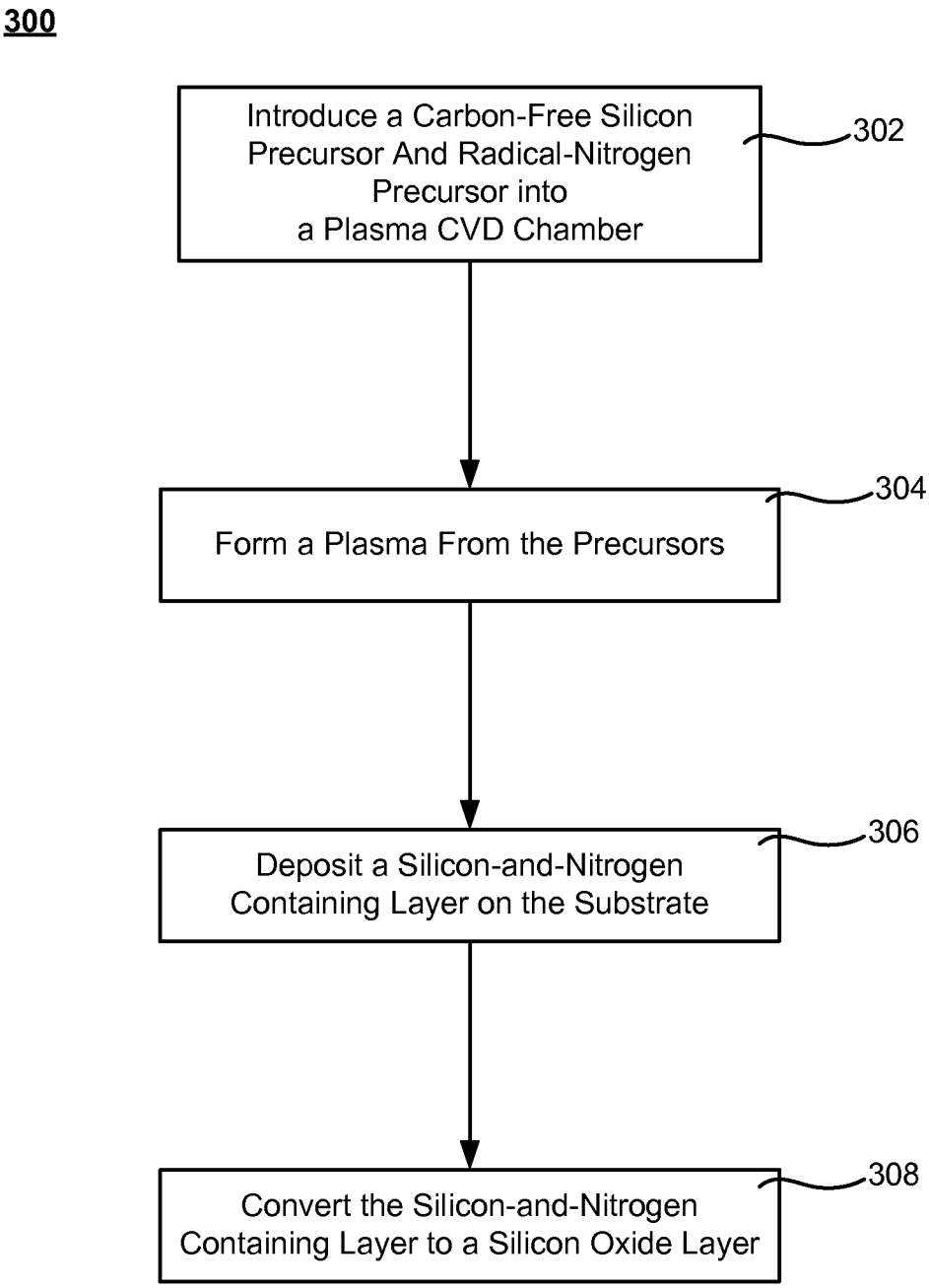

300
Introduce a Carbon-Free Silicon Precursor And Radical-Nitrogen Precursor into a Plasma CVD Chamber
302
Form a Plasma From the Precursors
304
Deposit a Silicon-and-Nitrogen Containing Layer on the Substrate
306
Convert the Silicon-and-Nitrogen Containing Layer to a Silicon Oxide Layer
308

FIG. 3

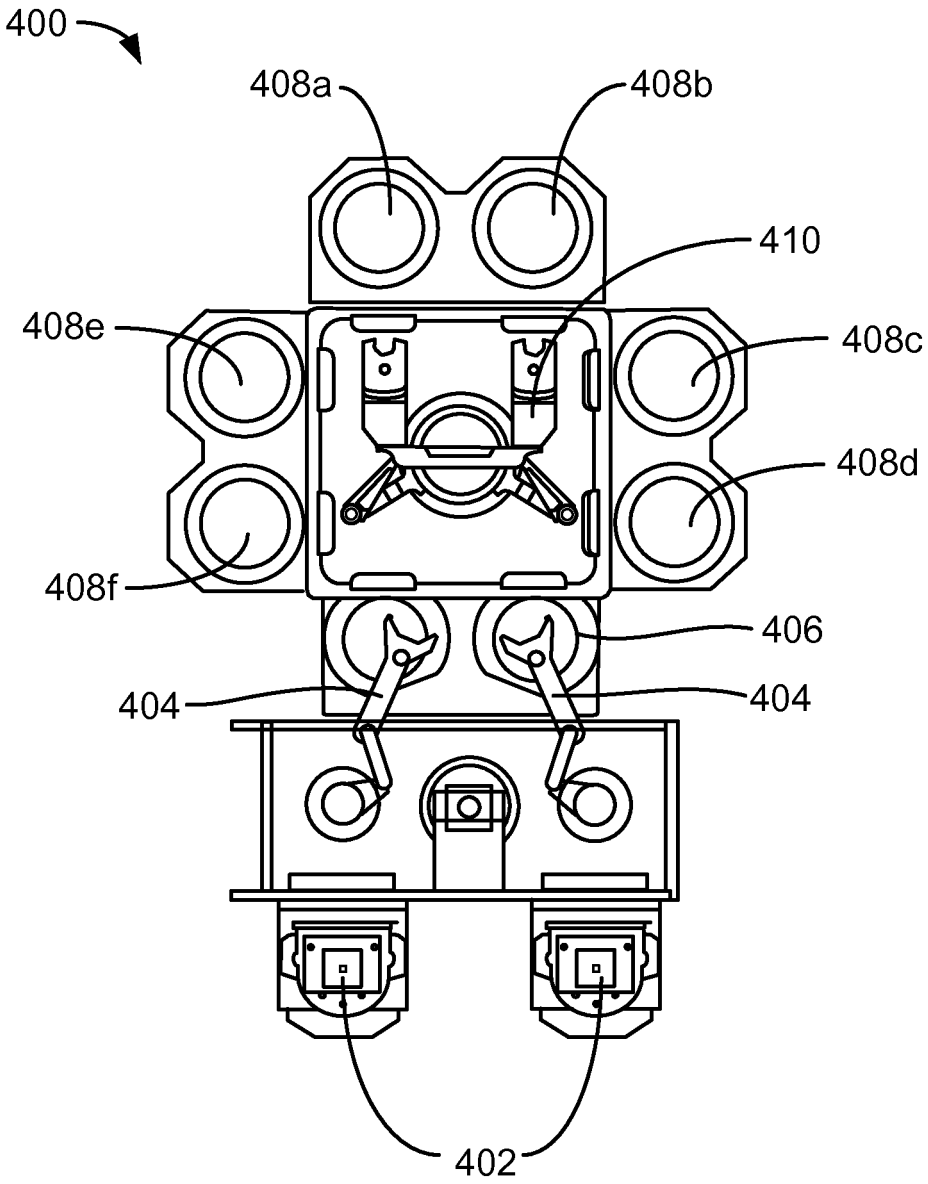


FIG. 4

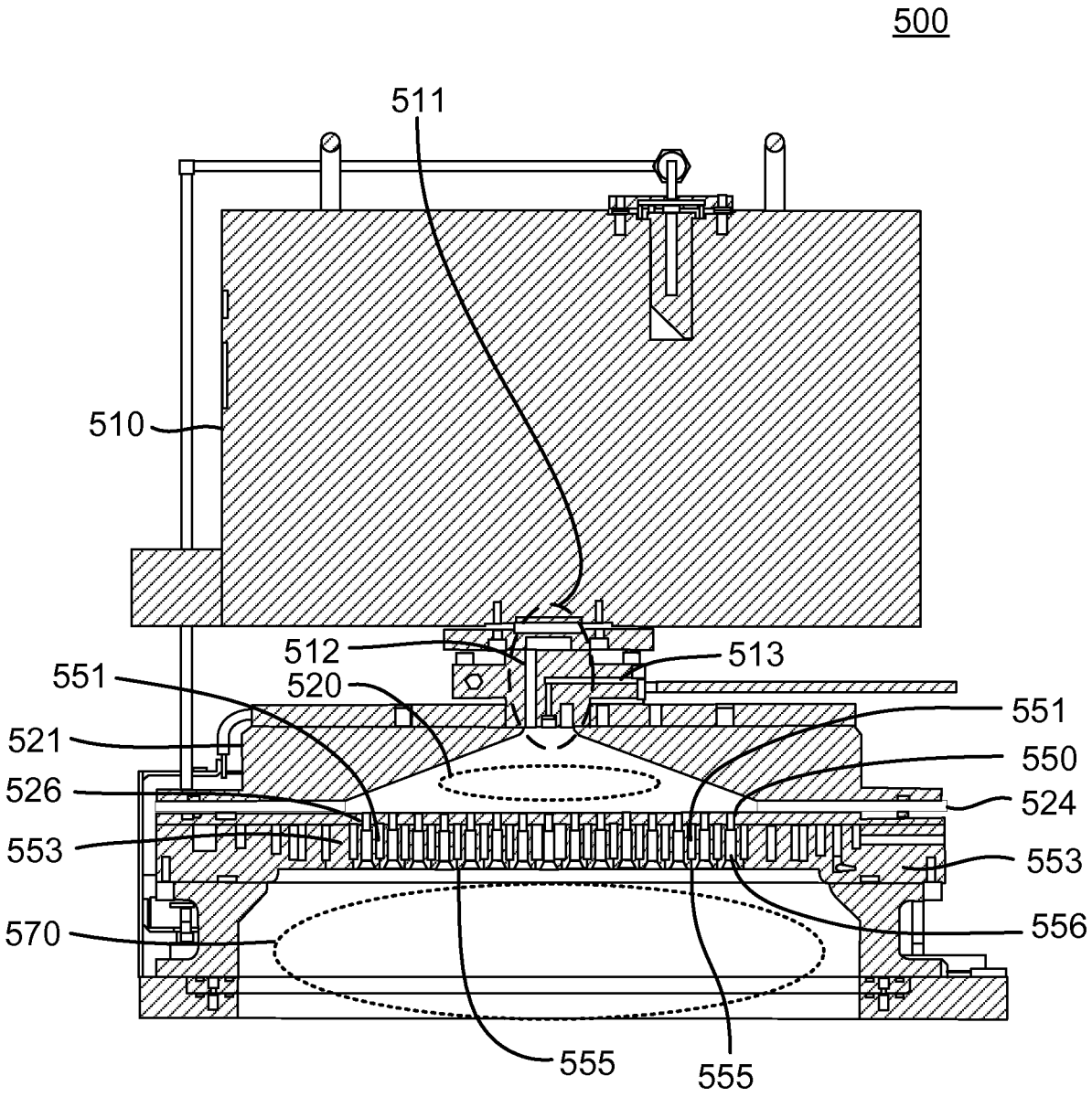

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FIG. 5A

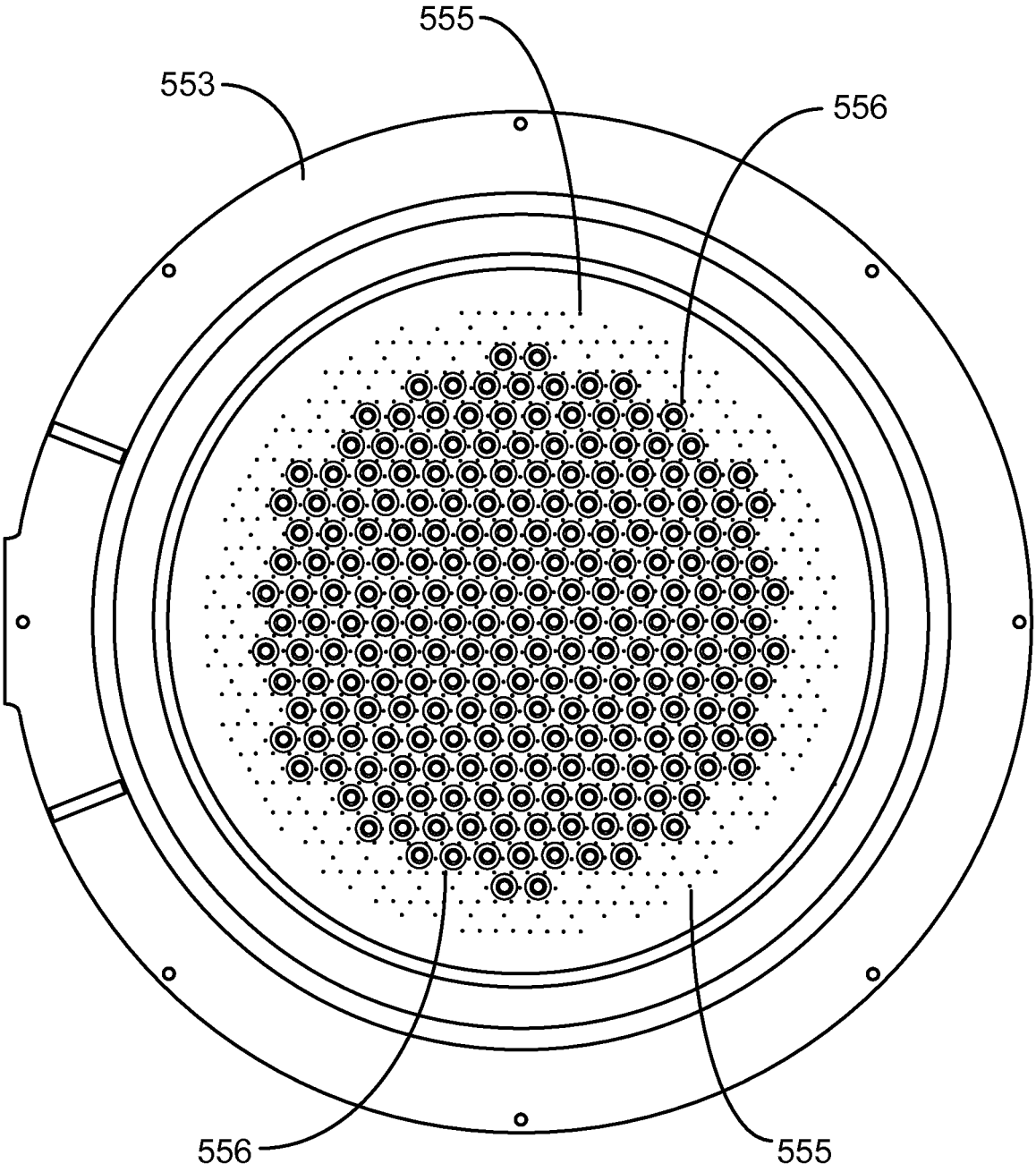


FIG. 5B